

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	4	wagganer near eric.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:24
2	BRS	L2	14	zhu near helen.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:26
3	BRS	L3	26	le near daniel.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:27

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	16035	(arc or anti-reflect\$3) near15 (dielectric or insulat\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:28
5	BRS	L5	557	((arc or anti-reflect\$3) near15 (dielectric or insulat\$3)) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:28
6	BRS	L6	370	(pattern\$3 or etch\$3 ) near15 ((arc or anti-reflect\$3) near15 (dielectric or insulat\$3)) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:28

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	370	(pattern\$3 or etch\$3) near15 ((arc or anti- reflect\$3) near15 (dielectric or insulat\$3)) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:29
8	BRS	L8	25	(pattern\$3 or etch\$3) near5 (selectivity) near15 ((arc or anti- reflect\$3) near15 (dielectric or insulat\$3)) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:47
9	BRS	L9	24	(etch\$3) near5 (selectivity) near15 ((arc or anti- reflect\$3) near15 (dielectric or insulat\$3)) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:48

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	266	(etch\$3) near15 ((arc or anti-reflect\$3) near15 (dielectric or insulat\$3)) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 11:48
11	BRS	L11	183	(etch\$3) near15 (arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 12:25
12	BRS	L12	29	(etch\$3) near15 (arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist) same (selectivity)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:30

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	26	(dielectric) near10 (photoresist near etch) near15 (selectivity)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:21
14	BRS	L14	0	(etch\$3) near15 (arc or anti-reflect\$3) near15 (thickness) near15 (dielectric) near25 (photoresist) same (selectivity)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:30
15	BRS	L15	0	(etch\$3) near15 (arc or anti-reflect\$3) near25 (thickness) near15 (dielectric) near25 (photoresist) same (selectivity)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:31

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	10	(etch\$3) near15 (arc or anti-reflect\$3) near15 (thickness) near15 (dielectric) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:31
17	BRS	L17	6	(etch\$3) near15 (arc or anti-reflect\$3) near5 (thickness) near15 (dielectric) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:32
18	BRS	L18	12	(etch\$3) near15 (arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist near10 thickness)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:23

	Type	L #	Hits	Search Text	DBs	Time Stamp
19	BRS	L19	0	(clean near etch\$3) near15 (arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist near10 thickness)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:37
20	BRS	L20	1	(clean near etch\$3) near15 (arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:37
21	BRS	L21	1	(clean near3 etch\$3) near15 (arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:38

	Type	L #	Hits	Search Text	DBs	Time Stamp
22	BRS	L22	0	(clean near3 etch\$3) same (arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:38
23	BRS	L23	0	(clean near3 etch\$3) same ((arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:38
24	BRS	L24	3	(clean\$3 near3 etch\$3) same ((arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:40

	Type	L #	Hits	Search Text	DBs	Time Stamp
25	BRS	L25	2	(clean\$3 near3 etch\$3) near35 ((arc or anti- reflect\$3) near15 (dielectric) near25 (photoresist))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 13:40
26	BRS	L26	4	(clean\$3 near3 etch\$3) near35 ((arc or anti- reflect\$3) near15 (dielectric))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:39
27	BRS	L27	44	(electrode near15 etch\$3) near35 ((arc or anti-reflect\$3) near15 (dielectric))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:07

	Type	L #	Hits	Search Text	DBs	Time Stamp
28	BRS	L28	0	(tempearature near15 electrode near15 etch\$3) near35 ((arc or anti-reflect\$3) near15 (dielectric))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:09
29	BRS	L29	0	(temperature near15 electrode near15 etch\$3) near35 ((arc or anti-reflect\$3) near15 (dielectric))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:09
30	BRS	L30	1	(heat\$3 near15 electrode near15 etch\$3) near35 ((arc or anti-reflect\$3) near15 (dielectric))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:10

	Type	L #	Hits	Search Text	DBs	Time Stamp
31	BRS	L31	0	(electrode near15 etch\$3 near5 chamber) near35 ((arc or anti- reflect\$3) near15 (dielectric))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:11
32	BRS	L32	0	(electrode) near15 (etch\$3 near chamber) near35 ((arc or anti- reflect\$3) near15 (dielectric))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:11
33	BRS	L34	0	(temperature near15 electrode) near15 (etch\$3 near chamber) near15 (dielectric)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
34	BRS	L35	0	(heat\$3 near15 electrode) near15 (etch\$3 near chamber) near15 (dielectric)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:12
35	BRS	L33	40	(electrode) near15 (etch\$3 near chamber) near15 (dielectric)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:12
36	BRS	L36	0	(opposite near electrode) near15 (etch\$3 near chamber) near15 (dielectric)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
37	BRS	L37	0	(oppos\$4 near electrode) near15 (etch\$3 near chamber) near15 (dielectric)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:13
38	BRS	L38	12	(etch\$3) near15 (arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist) near10 (angst\$3 or thickness)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:24
39	BRS	L39	0	(etch\$3) near15 (arc or anti-reflect\$3) near15 (dielectric) near25 (photoresist) near10 (angs\$5)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:24

	Type	L #	Hits	Search Text	DBs	Time Stamp
40	BRS	L40	5615	(etch near selectivity)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:39
41	BRS	L41	83	(etch near selectivity) near15 (photoresist) near15 (dielectric)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:39
42	BRS	L42	7	((etch near selectivity) near15 (photoresist) near15 (dielectric)) same (trench)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/2 5 15:40

	<b>U</b>	<b>1</b>	<b>Document ID</b>	<b>Title</b>	<b>Current OR</b>
1	X		US 20040023484 A1	METHOD OF DEEP CONTACT FILL AND PLANARIZATION FOR DUAL DAMASCENE STRUCTURES	438/636
2	X		US 20040009672 A1	Method for etching a trench through an anti- reflective coating	438/694
3	X		US 20030003756 A1	METHOD FOR FORMING CONTACT BY USING ARF LITHOGRAPHY	438/706
4	X		US 20020173160 A1	Plasma etching of organic antireflective coating	438/717
5			US 6743726 B2	Method for etching a trench through an anti- reflective coating	438/694

	<b>U</b>	<b>1</b>	<b>Document ID</b>	<b>Title</b>	<b>Current OR</b>
6			US 6720252 B2	Method of deep contact fill and planarization for dual damascene structures	438/636
7			US 6630407 B2	Plasma etching of organic antireflective coating	438/717
8			US 6524964 B2	Method for forming contact by using ArF lithography	438/736
9			US 6440640 B1	Thin resist with transition metal hard mask for via etch application	430/314
10			US 6165695 A	Thin resist with amorphous silicon hard mask for via etch application	430/314
11			US 6162587 A	Thin resist with transition metal hard mask for via etch application	430/314

	U	1	Document ID	Title	Current OR
12			US 6127070 A	Thin resist with nitride hard mask for via etch application	430/5